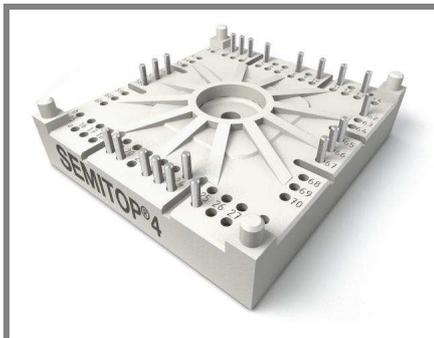


SK50GD12T4T



SEMITOP® 4

IGBT Module

SK50GD12T4T

Target Data

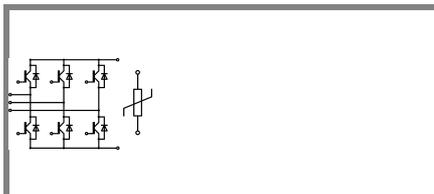
Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

- $V_{CE,sat}$, V_F = chip level value

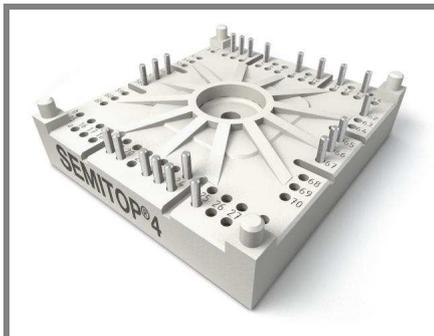


GD-T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	1200	V
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	75 A
		$T_s = 70\text{ °C}$	60 A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	150	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 800\text{ V}$; $V_{GE} \leq 15\text{ V}$; $T_j = 150\text{ °C}$ $V_{CES} < 1200\text{ V}$	10	μs
Inverse Diode			
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	60 A
		$T_s = 70\text{ °C}$	45 A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	150	A
I_{FSM}	$t_p = 10\text{ ms}$; half sine wave $T_j = 150\text{ °C}$	265	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +175	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1,7\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,01	mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$		600	nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	1,1	1,3	V
		$T_j = 150\text{ °C}$	1	1,2	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	15		$\text{m}\Omega$
		$T_j = 150\text{ °C}$	25		$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 50\text{ A}$, $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,85	2,05	V
		$T_j = 150\text{ °C}_{chiplev.}$	2,25	2,45	V
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	2,77		nF
C_{oes}			0,2		nF
C_{res}			0,16		nF
Q_G	$V_{GE} = -7\text{ V} \dots +15\text{ V}$		375		nC
R_{Gint}	$T_j = 25\text{ °C}$		4		Ω
$t_{d(on)}$	$R_{Gon} = 32\ \Omega$ $di/dt = 920\text{ A}/\mu\text{s}$	$V_{CC} = 600\text{ V}$ $I_C = 50\text{ A}$	63		ns
t_r			65		ns
E_{on}			8,3		mJ
$t_{d(off)}$	$R_{Goff} = 32\ \Omega$ $di/dt = 920\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$ $V_{GE} = \pm 15\text{ V}$	521		ns
t_f			80		ns
E_{off}			5		mJ
$R_{th(j-s)}$	per IGBT		0,65		K/W

SK50GD12T4T



SEMITOP® 4

IGBT Module

SK50GD12T4T

Target Data

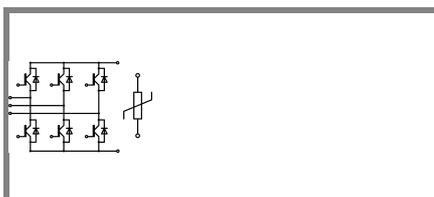
Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

- $V_{CE,sat}$, V_F = chip level value



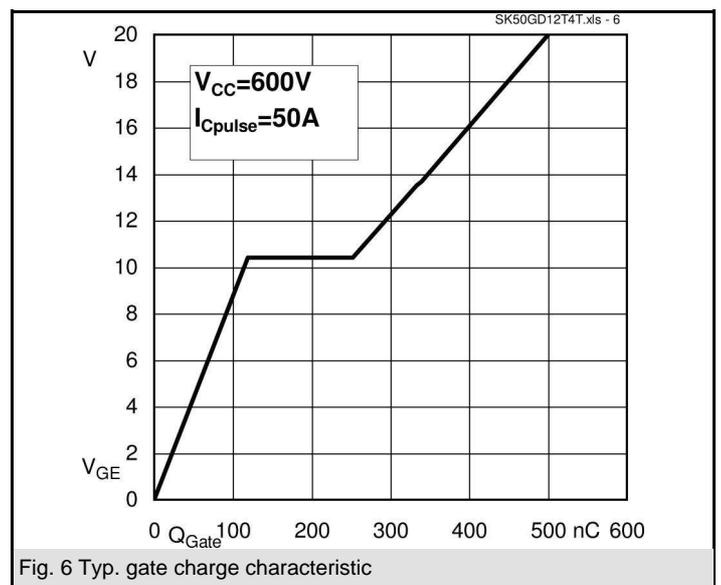
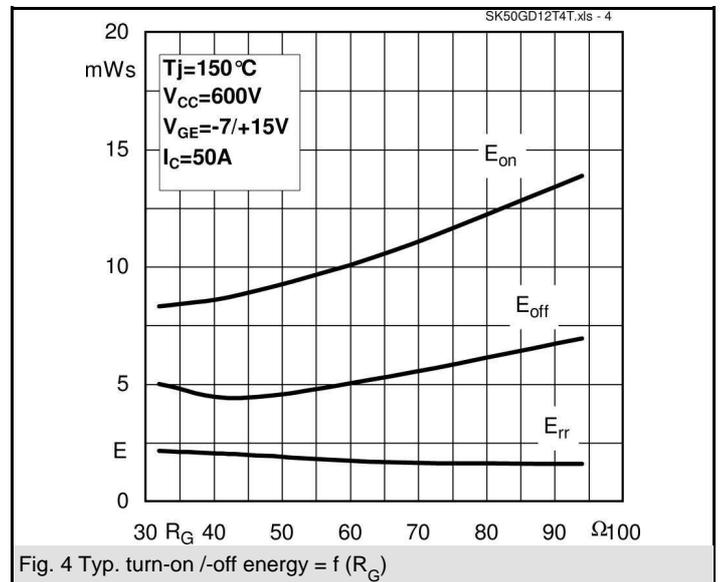
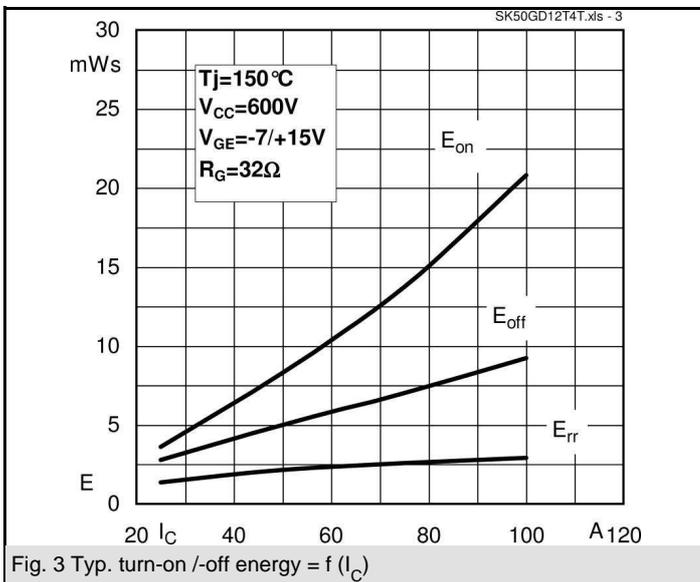
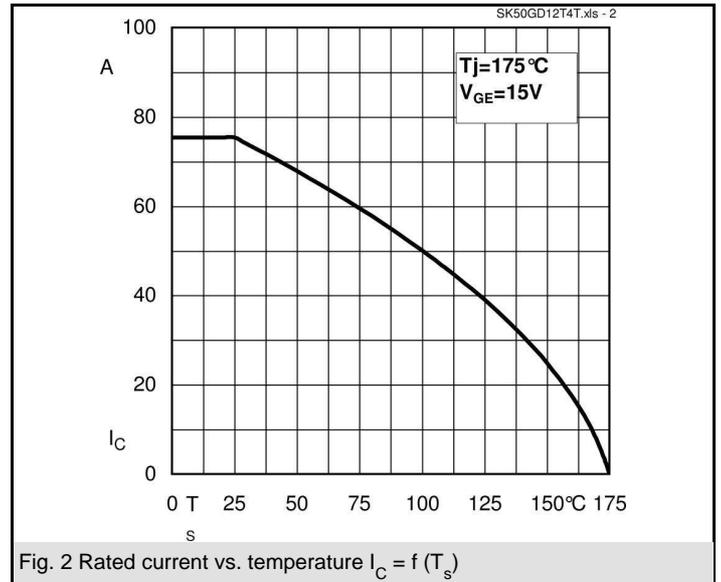
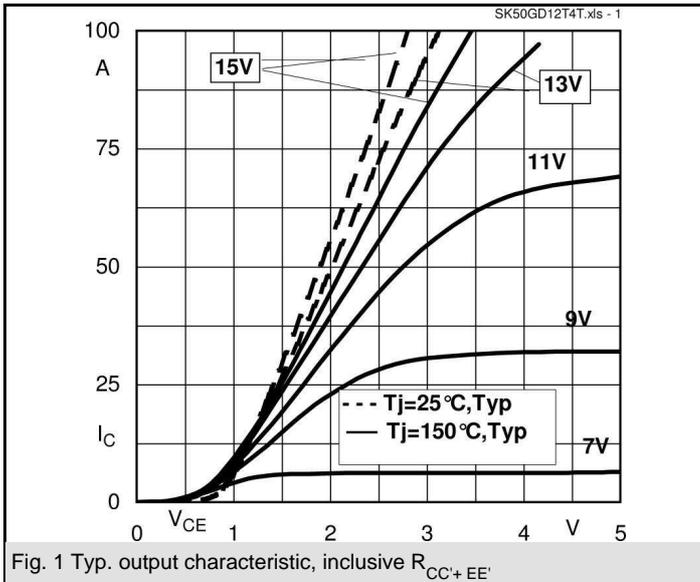
GD-T

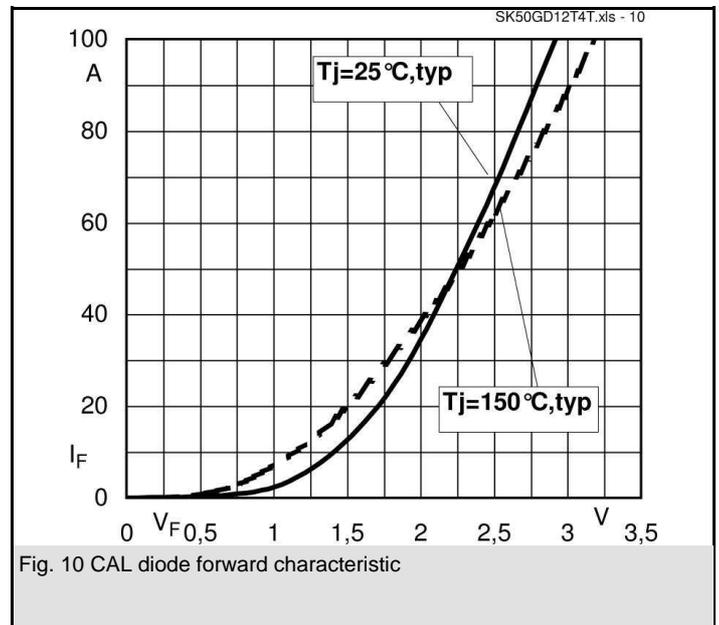
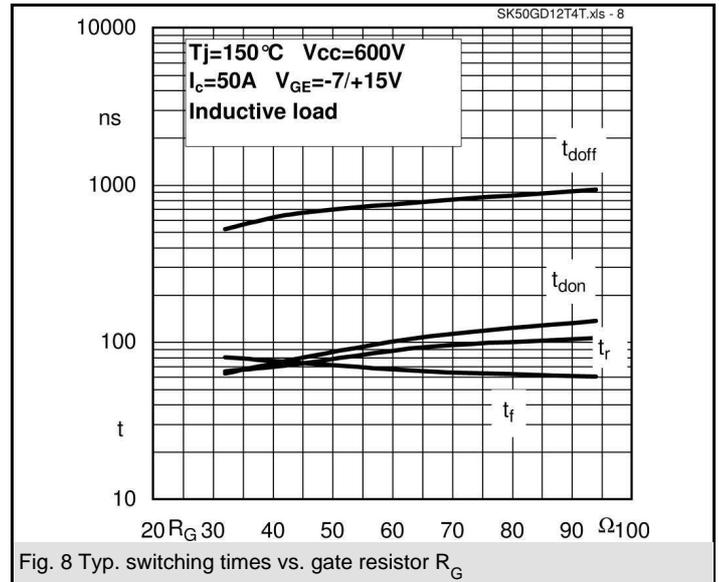
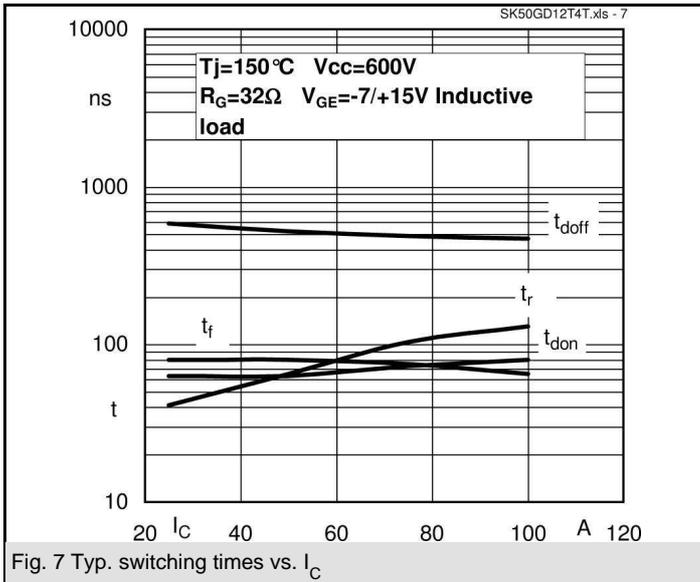
Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	2,2	2,55	V
		$T_j = 150 \text{ }^\circ\text{C}_{chiplev.}$	2,18	2,5	V
V_{F0}		$T_j = 25 \text{ }^\circ\text{C}$	1,3	1,5	V
		$T_j = 150 \text{ }^\circ\text{C}$	0,9	1,1	V
r_F		$T_j = 25 \text{ }^\circ\text{C}$	19	21	mΩ
		$T_j = 150 \text{ }^\circ\text{C}$	26	28	mΩ
I_{RRM}	$I_F = 50 \text{ A}$		30		A
Q_{rr}	$di/dt = 920 \text{ A}/\mu\text{s}$		7,2		μC
E_{rr}	$V_{CC} = 600\text{V}$		2,15		mJ
$R_{th(j-s)D}$	per diode		0,97		K/W
M_s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100^\circ\text{C}$ ($R_{25} = 5\text{k}\Omega$)		493±5%		Ω

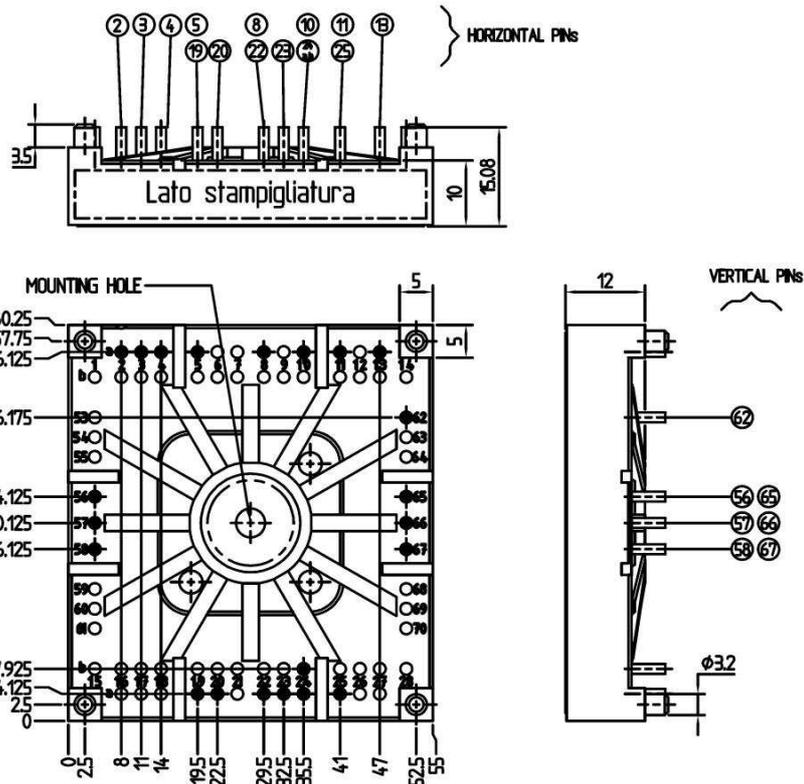
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

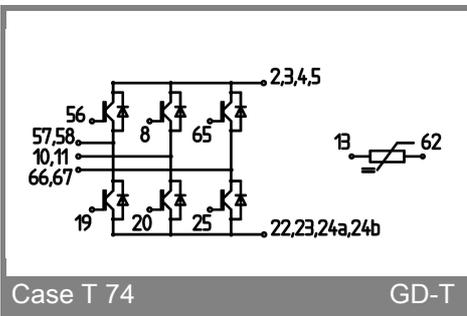




SK50GD12T4T



Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T